

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,273,533 B2
APPLICATION NO. : 10/717268
DATED : September 25, 2007
INVENTOR(S) : Brcka et al.

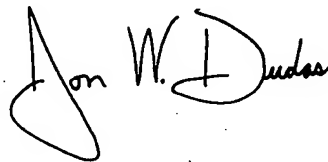
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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page, (56) under the "References Cited" section, "6,685,799 B2* 2/2004 Hooshdaran et al." should read --6,685,799 B2* 2/2004 Davis et al.--.
Col. 2, line 31, "torroids," should read --toroids,--.
Col. 2, line 35, "by the present applicant" should read --by the present applicants--.
Col. 2, line 39, "are becoming of increase demand" should read --are becoming of increased demand--.
Col. 2, line 51, "processing of 300 mm wafer." should read --processing of 300 mm wafers.--.
Col. 5, line 4, "low flux channels, are" should read --low flux channels are--.
Col. 8, line 23, "Applicant has proposed" should read --Applicants have proposed--.
Col. 10, line 3, "of the rf power deposited into" should read --of the RF power deposited into--.
Col. 10, line 45, "(FIG. 2O and 2F)" should read --(FIGS. 2D and 2F)--.

Signed and Sealed this

Eleventh Day of November, 2008

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a cursive "Dudas".

JON W. DUDAS
Director of the United States Patent and Trademark Office